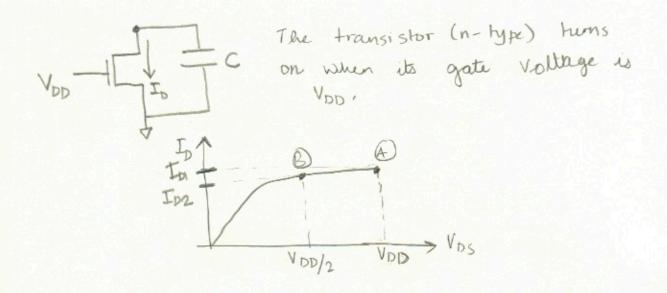
Equivalent resistance when (DIS) Charging through a transistor



Represent the transistor-capacitor circuit as an R-C network as follows:-

What is Req!

Reg: - Equivalent on- resistance of the transistor. Req = 1 Ron, initial + Ron, Final]

when the output is at VDD output is at $\frac{V_{DD}}{2}$ [Point (in Figure] [Point (in Figure]

Ron, initial =
$$\frac{V_{DD}}{I_{D1}}$$
 = $\frac{V_{DD}}{I_{DSat}}$ (1+ λV_{DD})

Ron, final = $\frac{V_{DD}/2}{I_{D2}}$ = $\frac{V_{DD}/2}{I_{DSat}}$ (1+ $\lambda V_{DD}/2$)

$$\frac{1}{I_{DSat}} = \frac{1}{2} I_{A} I_{A} Cox \left(\frac{W}{L}\right) \left[(V_{GS} - V_T) \right]^2$$

So,

Req = $\frac{1}{2} \left[\frac{V_{DD}}{I_{DSat}} + \frac{V_{DD}/2}{I_{DSat}} (I + \lambda V_{DD}/2) \right]$

Do some algebra when $\lambda V_{DD} < 1$

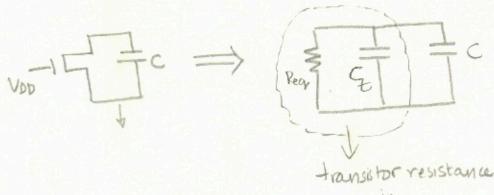
We can show

$$\frac{1}{4 I_{DSat}} \left(1 - \frac{5}{6} \lambda V_{DD} \right)$$

Req = $\frac{3V_{DD}}{4 I_{DSat}} \left(1 - \frac{5}{6} \lambda V_{DD} \right)$

Increasing the transistor size increases Itsat. Hence, it reduces Req and the time constant of charging and discharging a upacitor.

Of course, you're using more area on the die, which is not good (its expensione) but we'll see later that increasing transistor size also increases the transistor capacitance that is related with the structure of the transistor. So in reality the equivalent arount on the previous page should look like;



parallel with transistor capacitance. Ct:-transistor capacitance. Reg = Ct T C time constant of discharging the capacitor will be T = Reg (Ct + C) When Ct << C then T = Req C Both Reg and Ct depend on transistor (t) (W) 1 Reg & CE 1 So one must choose (w) wisely to obtain a certain I as specified by the end user.